

**Listing of Claims:**

This listing of claims replaces all prior versions and listings of claims in the application.

1. (Amended) A semiconductor device comprising:
  - a source, a gate and a drain;
  - a source-drain depletion region in a substrate under the gate;
  - a single deep-pocket ion implant in the source-drain depletion region at a drain side; and
  - a single shallow-pocket ion implant in the source-drain depletion region at a source side.
2. - 14. (Canceled)
15. (Amended) The semiconductor device as recited in claim 1 ~~[[0]]~~, further comprising:
  - a secondary deep-pocket ion implant in a source side of the source-drain depletion region, the secondary deep-pocket ion implant having been countered by ions of the source; and
  - a secondary shallow-pocket ion implant in a drain side of the source-drain depletion region, the secondary shallow-pocket ion implant having been countered by ions of the drain.
16. (Amended) The semiconductor device as recited in claim ~~[[1]]~~ 22, further comprising:
  - a secondary deep-pocket ion implant in a drain side of the source-drain depletion region, the secondary deep-pocket ion implant having been countered by ions of the drain; and
  - a secondary shallow-pocket ion implant in a source side of the source-drain depletion region, the secondary shallow-pocket ion implant having been countered by ions of the source.
17. - 21. (Canceled)
22. (New) A semiconductor device comprising:
  - a source, a gate and a drain;
  - a source-drain depletion region in a substrate under the gate;

a single deep-pocket ion implant in the source-drain depletion region at a source side; and  
a single shallow-pocket ion implant in the source-drain depletion region at a drain side.